SDB3101F

Schottky Barrier Diode

Features

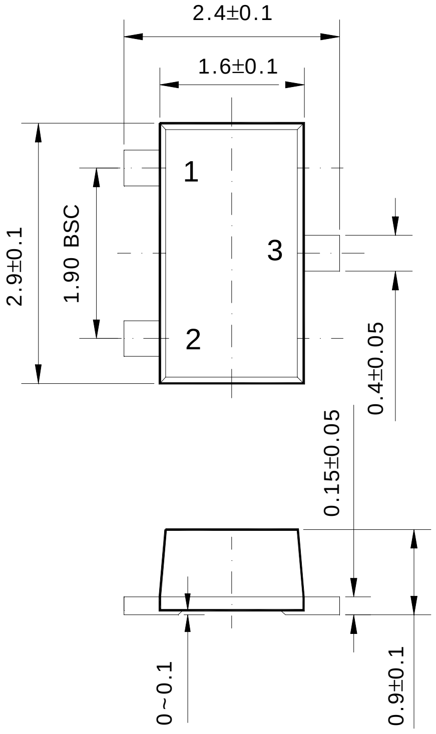
- Low power rectified
- Silicon epitaxial type
- High reliability

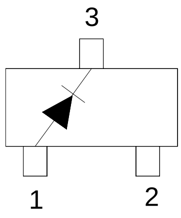
Ordering Information

Type No.	Marking	Package Code
SDB3101F	DB1	SOT-23F

Outline Dimensions

unit : mm





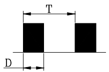
PIN Connections
1. Anode
2. NC
3. Cathode

Absolute maximum ratings

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Reverse voltage	V_R	30	V
Repetitive peak forward current	I_{FRM}^*	0.5	A
Forward current	I_F	0.2	A
Non-repetitive peak forward current(10ms)	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ 150	°C

* : δ = D/T =0.33
(T<1S)



Electrical Characteristics

Ta=25°C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage 1	$V_{F(1)}$	I_F=10mA	-	-	0.4	V
Forward voltage 2	$V_{F(2)}$	I_F=30mA	-	-	0.5	V
Reverse current	I_R	V_R=30V	-	-	1	μA
Total capacitance	C_T	V_R=1V, f=1MHz	-	-	10	pF
Reverse recovery time	t_{rr}	I_F= I_R=10mA, I_{RR}= 1mA, R_L=100Ω	-	-	5	ns

Electrical Characteristic Curves

Fig. 1 I_F-V_F

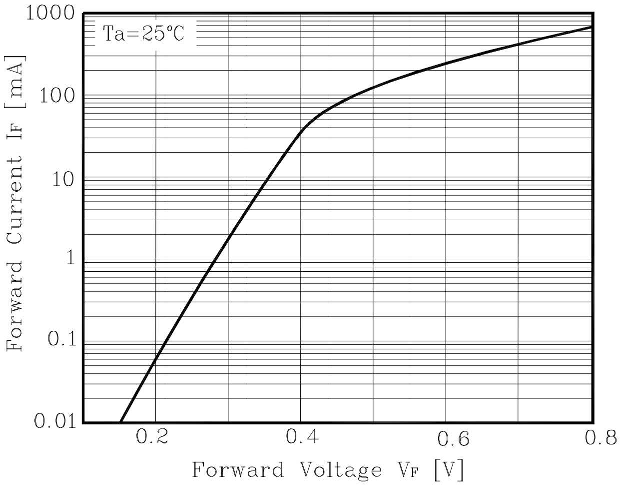


Fig. 2 I_R -V_R

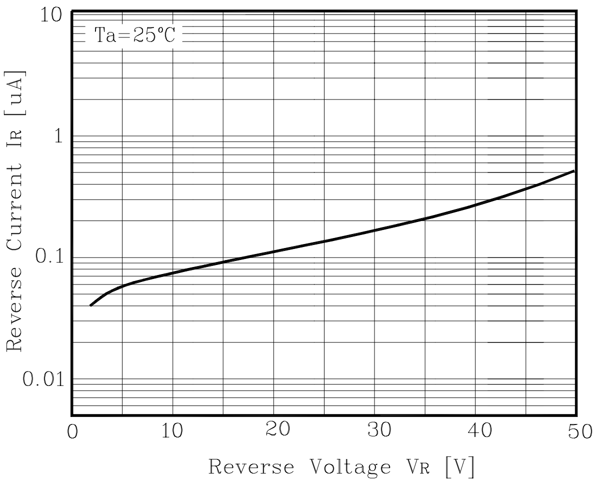


Fig. 3 C_T-V_R